

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a non-single-crystal semiconductor film, a support substrate that supports the non-single-crystal semiconductor film, and an active device having a part of the non-single-crystal semiconductor film as a channel region. In particular, the channel region has an oxygen concentration not higher than 1×10^{18} atoms/cm³ and a carbon concentration not higher than 1×10^{18} atoms/cm³.